

Silicon PNP Power Transistors

BD240/A/B/C

DESCRIPTION

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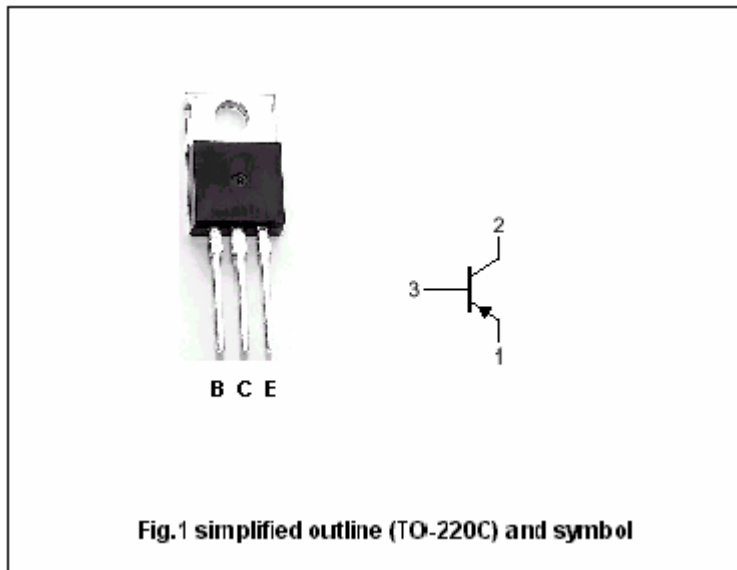
- With TO-220C package
- Complement to type BD239/A/B/C

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD240	-55	V
		BD240A	-70	
		BD240B	-90	
		BD240C	-115	
V _{CEO}	Collector-emitter voltage	BD240	-45	V
		BD240A	-60	
		BD240B	-80	
		BD240C	-100	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-4	A
I _B	Base current		-0.6	A
P _C	Collector power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	BD240	-45			V	
		BD240A	-60				
		BD240B	-80				
		BD240C	-100				
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1\text{ A}; I_B=-0.2\text{ A}$			-0.7	V	
V_{BE}	Base-emitter on voltage	$I_C=-1\text{ A}; V_{CE}=-4\text{ V}$			-1.3	V	
I_{CEO}	Collector cut-off current	BD240/A	$V_{CE}=-30\text{ V}; I_B=0$			-0.3	mA
		BD240B/C	$V_{CE}=-60\text{ V}; I_B=0$				
I_{CES}	Collector cut-off current	BD240	$V_{CE}=-45\text{ V}; V_{BE}=0$			-0.2	mA
		BD240A	$V_{CE}=-60\text{ V}; V_{BE}=0$				
		BD240B	$V_{CE}=-80\text{ V}; V_{BE}=0$				
		BD240C	$V_{CE}=-100\text{ V}; V_{BE}=0$				
I_{EBO}	Emitter cut-off current	$V_{EB}=-5\text{ V}; I_C=0$			-1	mA	
h_{FE-1}	DC current gain	$I_C=-0.2\text{ A}; V_{CE}=-4\text{ V}$	40				
h_{FE-2}	DC current gain	$I_C=-1\text{ A}; V_{CE}=-4\text{ V}$	15				

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PACKAGE OUTLINE

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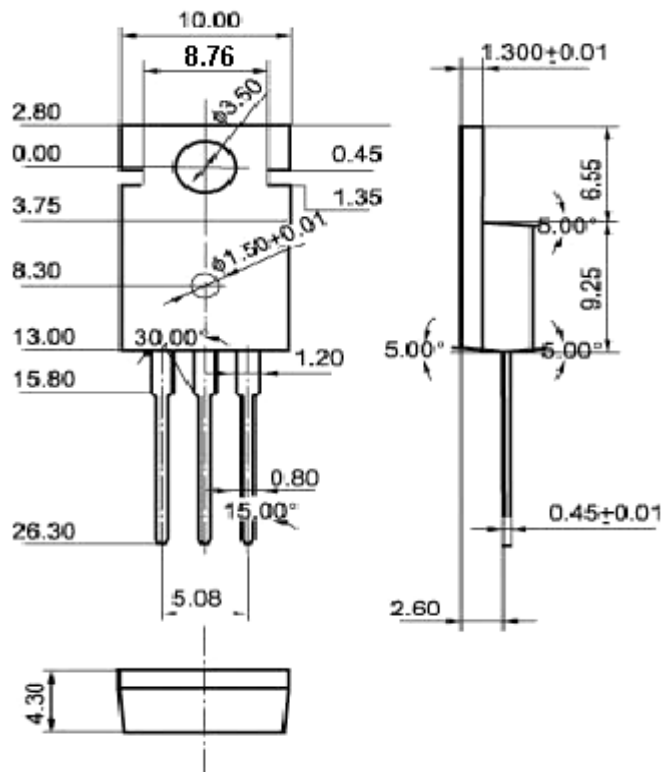


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)